

2SC790

SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

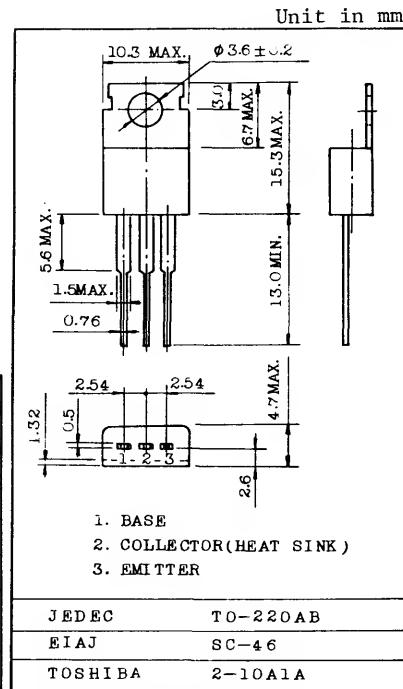
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- Complementary to 2SA490.
- Recommended for 10W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta=25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---------------------------------------|------------------|-----------|------|
| Collector-Base Voltage | V _{CBO} | 50 | V |
| Collector-Emitter Voltage | V _{CEO} | 40 | V |
| Emitter-Base Voltage | V _{EBO} | 5 | V |
| Collector Current | I _C | 3 | A |
| Emitter Current | I _E | -3 | A |
| Collector Power Dissipation (Tc=25°C) | P _C | 25 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | T _{stg} | -55 ~ 150 | °C |



Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|-------------------------------|---|------|------|------|------|
| Collector Cut-off Current | I _{CBO} | V _{CB} =30V, I _E =0 | - | - | 10 | μA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} =5V, I _C =0 | - | - | 100 | μA |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | I _C =50mA, I _B =0 | 40 | - | - | V |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | I _E =10mA, I _C =0 | 5 | - | - | V |
| DC Current Gain | h _{FE} (1) (Note) | V _{CE} =2V, I _C =0.5A | 40 | - | 240 | |
| | h _{FE} (2) | V _{CE} =2V, I _C =2A | 13 | - | - | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C =2A, I _B =0.2A | - | 0.25 | 1.4 | V |
| Base-Emitter Voltage | V _{BE} | V _{CE} =2V, I _C =2A | - | 0.85 | 1.8 | V |
| Transition Frequency | f _T | V _{CE} =2V, I _C =0.5A | 3 | 10 | - | MHz |
| Collector Output Capacitance | C _{ob} | V _{CB} =10V, I _E =0, f=1MHz | - | 85 | - | pF |

Note: h_{FE}(1) Classification R : 40 ~ 80, O : 70 ~ 140, Y : 120 ~ 240